Ordering number : ENN6582

N-Channel Silicon MOSFET

FSS239

Load Switching Applications

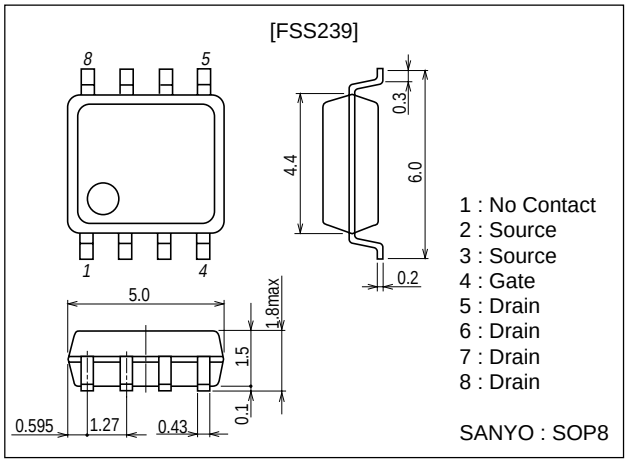
Features

- Low ON resistance.
- 2.5V drive.

Package Dimensions

unit : mm

2185



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		7	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	52	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (1000mm²×0.8mm)	1.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	0.4		1.3	V
Forward Transfer Admittance	|yfs|	V_{DS}=10V, I_D=7A	10.9	15.5		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=7A, V_{GS}=4V		24	32	mΩ
	R_{DS}(on)2	I_D=2A, V_{GS}=2.5V		29	42	mΩ

Marking : S239

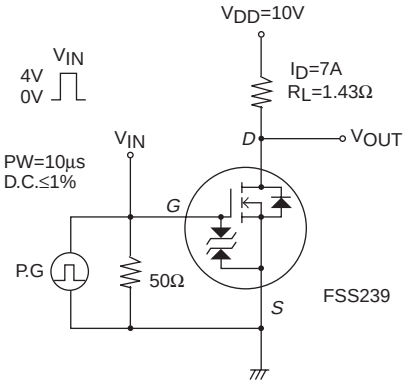
Continued on next page.

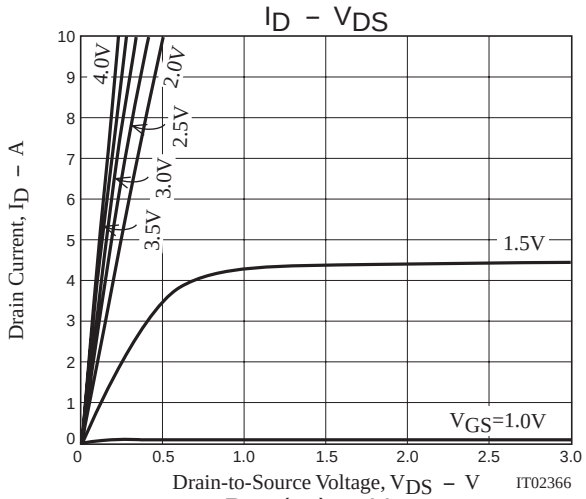
SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

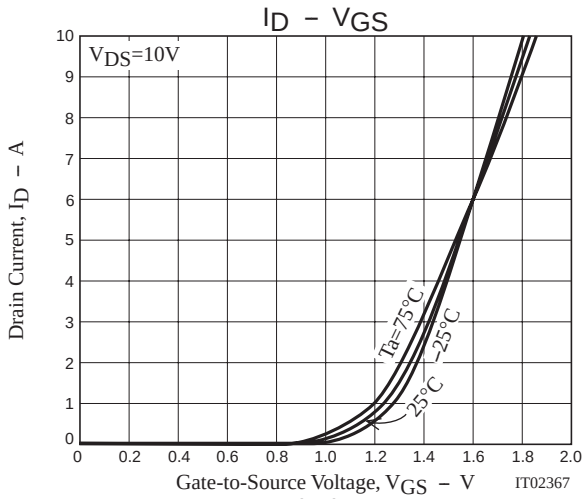
Continued from preceding page.

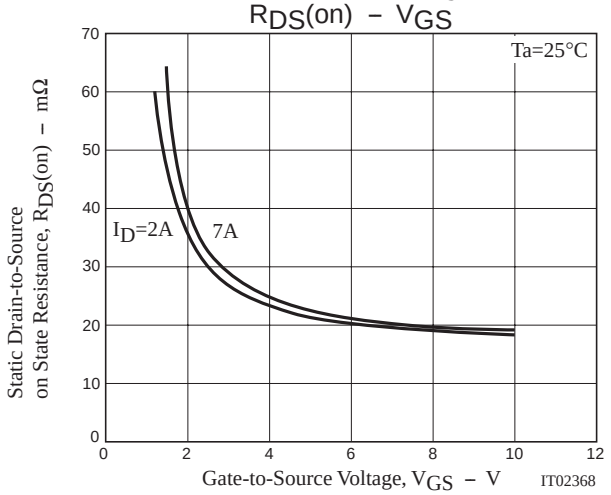
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		900		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		260		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		200		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit		15		ns
Rise Time	t_{r}	See specified Test Circuit		220		ns
Turn-OFF Delay Time	t_{d}(off)	See specified Test Circuit		75		ns
Fall Time	t_{f}	See specified Test Circuit		180		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_{D}=7A		32		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=10V, I_{D}=7A		1.7		nC
Gate-to-Drain "Miller" Charge	Qgd	V_{DS}=10V, V_{GS}=10V, I_{D}=7A		6.4		nC
Diode Forward Voltage	V_{SD}	I_{S}=7A, V_{GS}=0		0.86	1.2	V

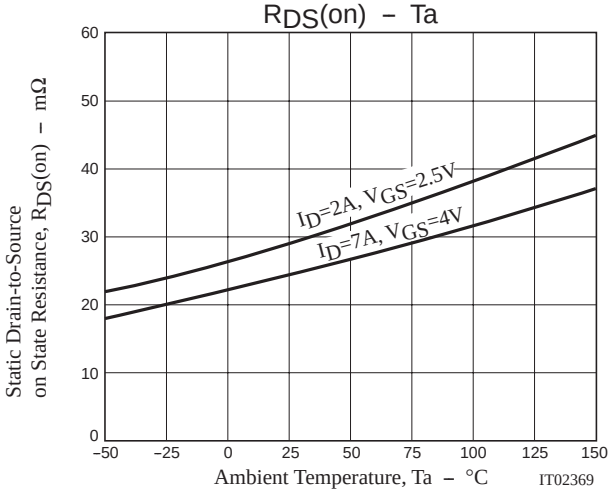
Switching Time Test Circuit

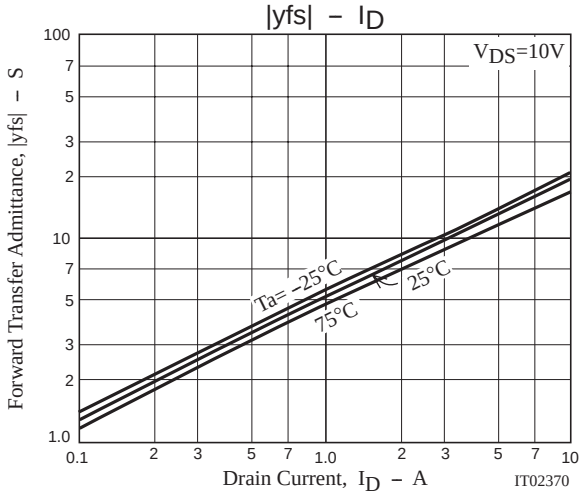


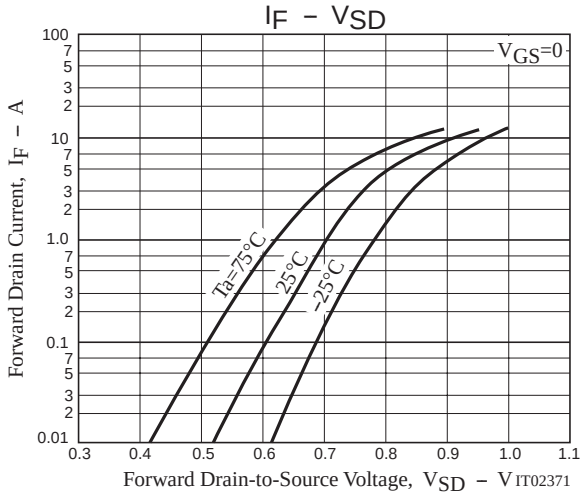


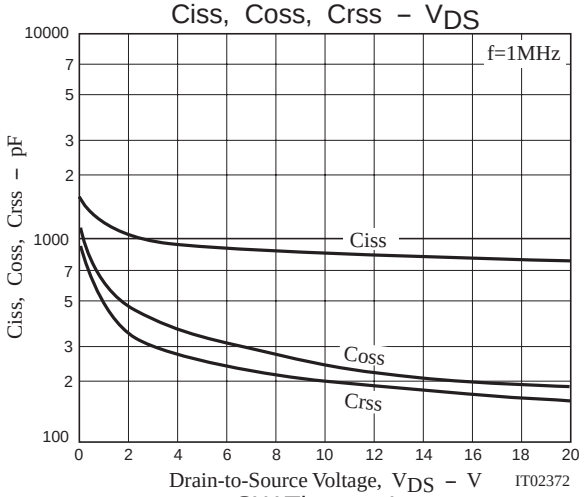


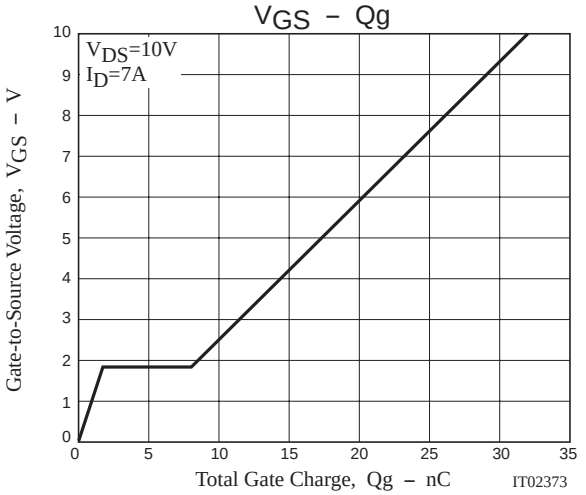


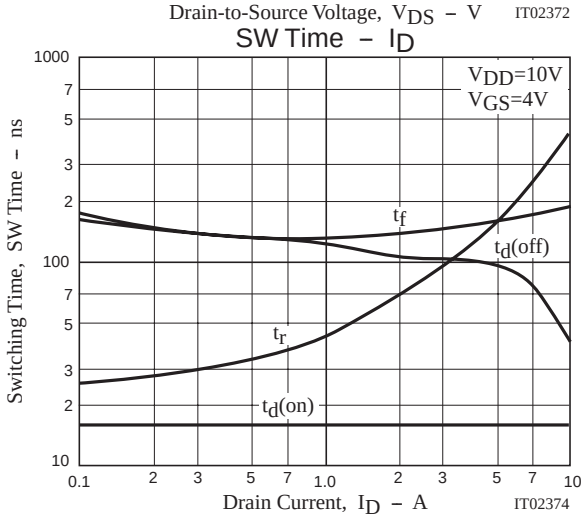


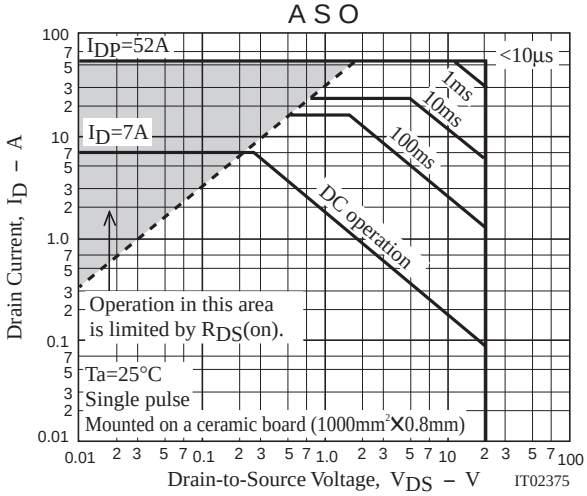

|yfs| – ID
VDS=10V
Ta= –25°C
25°C
75°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT02370

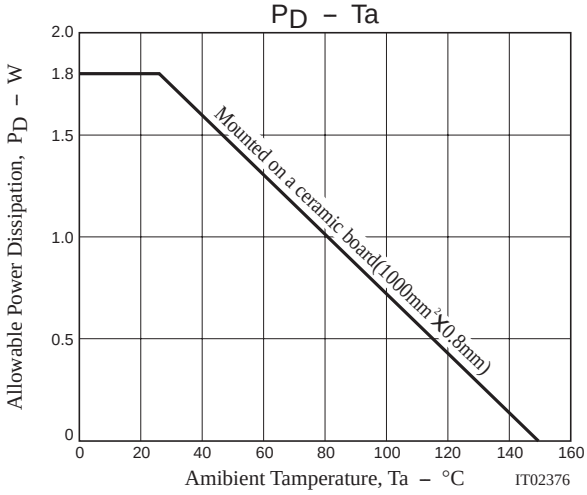

IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Drain Current, IF – A
Forward Drain-to-Source Voltage, VSD – V
IT02371


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT02372


VGS – Qg
VDS=10V
ID=7A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT02373


SW Time – ID
VDD=10V
VGS=4V
tf
td(off)
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT02374


A S O
IDP=52A
<10μs
1ms
10ms
100ms
DC operation
ID=7A
Operation in this area
is limited by RDS(on).
Ta=25°C
Single pulse
Mounted on a ceramic board (1000mm²×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT02375


PD – Ta
Mounted on a ceramic board(1000mm²×0.8mm)
Allowable Power Dissipation, PD – W
Amibient Tamperature, Ta – °C
IT02376